



Press release – May 26th, 2003

Altis Semiconductor ready to start MRAM R&D Program

Showing a great “Savoir-faire”, Altis Semiconductor has been elected by its Shareholders IBM/Infineon to make a push forward from MRAM fundamental development to an industrial era.

Starting mid 2003, Altis Semiconductor will be hosting on its site near Paris (France) the next Research and Development stages for high density MRAM (Magnetic Random Access Memory), in support to its Shareholders and Parent Companies’ strategy, IBM and Infineon. Infineon Technologies will there further develop together with Altis Semiconductor this emerging non-volatile technology at Altis. In addition, Infineon Technologies and IBM will continue to collaborate on the development of this technology.

Aimed at enhancing R&D efforts efficiency, the Altis’ project is part of a global cooperation between different IBM and Infineon locations around the world. More specifically, it will play a leading role in bringing this new device concept from the fundamental R&D stage to the industrial phase.

The location of Altis makes it easy to collaborate with key French universities. The discovery place of the GMR (Giant Magneto Resistance) effect is the university of Orsay.

“Two elements were instrumental in bringing this new program here in Altis: the proximity of the world-class R&D campus of Orsay and the recognition of our engineers expertise combined with our world-class operational results on copper leading-edge technologies” said Didier Lamouche, CEO of Altis Semiconductor.

“Altis Semiconductor is a major player in the leading-edge semiconductor arena, its ability to master the most advanced copper technologies is a key asset for the MRAM program” said Dr Wilhelm Beinvogl, CTO of the Memory Product Division, Infineon.

“Altis Semiconductor is a well-suited location to operate a smooth transition from lab science towards early manufacturing applications for the MRAM program” said Dr T. C. Chen, VP Science and Technology, IBM Research.

The MRAM concept

Who hasn’t dreamed of turning on her/his computer and having it come to life instantaneously just like a radio or TV? Not too far away from reality with the coming of MRAM technology. As its name suggests, MRAM uses magnetism instead of electrical charge to store data. Unlike conventional RAM, MRAM cells can thus maintain their state even when power is removed. MRAM can be considered as “universal memory”, offering the unique combination

of non-volatility and high endurance with excellent random access speed. The demand for a 'universal memory' is driven by mobile appliances and multimedia applications.

This new technology has the potential to replace today's memory technologies in electronic products of the future. It is a breakthrough memory technology that could significantly increase battery life of cell phones, games consoles, handheld devices, laptops and other battery powered products.

About Altis Semiconductor

Altis Semiconductor a joint venture between IBM Microelectronics Division and Infineon Technologies, was created in July 1999. Altis Semiconductor is located in Corbeil-Essonnes, France and employs directly 2 200 people. The company operates a SC technology campus hosting and additional 1 000 people from major SC industry-related companies.

Its leading-edge technology offering includes advanced Logic components down to 0.13 micron with Copper interconnects, eDRAM, mixed-signal and eFlash components.

With an investment portfolio of 1 billion Euros since 1999, Altis is delivering key devices for IBM and Infineon customers, industry leaders in the PC, telecom and consumer business market segments.

For more information: <http://www.altissemiconductor.com>

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